

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in this application.

**Listing of Claims:**

Claim 1 (Currently Amended):        A semiconductor memory element comprising:  
a substrate;  
a semiconductor circuit portion comprising ~~made of~~ an organic semiconductor disposed  
on the substrate; and  
a protection portion disposed adjacent to the semiconductor circuit portion, the protection  
portion being made of a material in which ~~capable of causing~~ a crack extending to the  
semiconductor circuit portion is formed after ~~due to~~ a predetermined means performs.

Claim 2 (Currently Amended):        A semiconductor memory element comprising:  
a substrate;  
a semiconductor circuit portion comprising ~~made of~~ an organic semiconductor disposed  
on the substrate;  
a protection portion disposed adjacent to the semiconductor circuit portion and including  
~~having~~ a window portion; and  
a ~~freely~~ strippable seal member for sealing the window portion of the protection portion.

Claim 3 (Currently Amended):        A semiconductor memory element comprising:  
a substrate;  
a semiconductor circuit portion comprising ~~made of~~ an organic semiconductor disposed  
on the substrate;  
a protection portion disposed adjacent to the semiconductor circuit portion; and  
a performance deterioration portion including a performance deterioration material for  
deteriorating a performance of the organic semiconductor and disposed adjacent to the protection

portion, the protection portion being made of a material in which ~~capable of causing~~ a crack extending to the semiconductor circuit portion is formed after ~~due to~~ a predetermined means performs.

Claim 4 (Currently Amended): The semiconductor memory element according to claim 1 ~~or 3~~, wherein the predetermined means is a mechanical punch means.

Claim 5 (Currently Amended): The semiconductor memory element according to claim 1 ~~or 3~~, wherein the predetermined means is a heating means.

Claim 6 (Currently Amended): The semiconductor memory element according to claim 1 ~~or 3~~, wherein the predetermined means is a pressurizing means.

Claim 7 (Currently Amended): The semiconductor memory element according to claim 1 ~~or 3~~, wherein the predetermined means is a light irradiation means.

Claim 8 (Currently Amended): A semiconductor memory element comprising:  
a substrate;  
a semiconductor circuit portion disposed on the substrate and comprising ~~made of~~ an organic semiconductor including a performance deterioration material for deteriorating a performance of the organic semiconductor after the performance deterioration is activated; and  
a protection portion disposed adjacent to the semiconductor circuit portion, wherein the performance deterioration material is activated by a predetermined means.

Claim 9 (Currently Amended): A semiconductor memory element comprising:  
a substrate;  
a semiconductor circuit portion disposed on the substrate and comprising ~~made of~~ an organic semiconductor including a performance deterioration material for deteriorating a performance of the organic semiconductor after the performance deterioration is activated; and

a film disposed adjacent to the semiconductor circuit portion, capable of obtaining light transmissive property due to an irradiation of light having a predetermined wavelength thereon, wherein

the performance deterioration material is activated by a predetermined means.

Claim 10 (Currently Amended): A semiconductor memory element comprising:  
a substrate;

a semiconductor circuit portion disposed on the substrate and comprising ~~made of~~ an organic semiconductor including a performance deterioration material for deteriorating a performance of the organic semiconductor after the performance deterioration is activated;

a protection portion disposed adjacent to the semiconductor circuit portion and including ~~having~~ a window portion; and

a ~~freely-strippable~~ seal member for sealing the window portion of the protection portion.

Claim 11 (Currently Amended): The semiconductor memory element according to claim ~~any one of claims 8 to 10~~, wherein

the performance deterioration material is encapsulated.

Claim 12 (Currently Amended): The semiconductor memory element according to claim 8 ~~or 9~~, wherein

the predetermined means is a pressurizing means.

Claim 13 (Currently Amended): The semiconductor memory element according to claim 8 ~~or 9~~, wherein

the predetermined means is a heating means.

Claim 14 (Original): The semiconductor memory element according to claim 9, wherein the predetermined means is an UV irradiation means.

Claim 15 (Original): The semiconductor memory element according to claim 9, wherein

the predetermined means is an electron beam irradiation means.

Claim 16 (Currently Amended): The semiconductor memory element according to claim 2 ~~or 10~~, wherein

the deterioration in the semiconductor circuit portion of the organic semiconductor is started by stripping off the seal member.

Claim 17 (Currently Amended): The semiconductor memory element according to claim ~~any one of claims 1 to 16~~, wherein

the semiconductor portion is a semiconductor portion in a range corresponding to a predetermined circuit portion of the semiconductor circuit portion.

Claim 18 (Original): The semiconductor memory element according to claim 17, wherein

the predetermined circuit portion is a data area.

Claim 19 (Original): The semiconductor memory element according to claim 17, wherein

the predetermined circuit portion is a management information area.

Claim 20 (Original): The semiconductor memory element according to claim 17, wherein

the predetermined circuit portion is an electric power shutdown switch.

Claim 21 (Original): The semiconductor memory element according to claim 17, wherein

the predetermined circuit portion is an encryption key record area.

Claim 22 (Currently Amended): A lifetime operation starting apparatus having a a ~~[[an]]~~ starting device for starting an operation of a semiconductor memory element using an

organic semiconductor, which has a seal attached to a position corresponding to a predetermined portion thereof, within a lifetime, comprising

the starting device being a seal strip off device for stripping off the [[a]] seal attached to a position corresponding to a predetermined portion of the organic semiconductor in order to deteriorate a performance of the organic semiconductor by bringing elements outside of the seal into contact with the organic semiconductor as the starting device.

Claim 23 (Currently Amended): A lifetime operation starting apparatus having a [[an]] starting device for starting an operation of a semiconductor memory element using an organic semiconductor, which is protected by a protection portion, within a lifetime, comprising, ~~in order to cause a crack in a protection portion protecting the organic semiconductor as the~~ starting device[[,]] being at least one of:

a mechanical punch device for punching a microhole through the protection portion to cause a crack in the protection portion;

a heating device for heating the protection portion to cause the crack in the protection portion;

a pressurizing device for pressurizing the protection portion to cause the crack in the protection portion; and

a light irradiation device for irradiating the protection portion with light to cause the crack in the protection portion.

Claim 24 (Currently Amended): A lifetime operation starting apparatus having a [[an]] starting device for starting an operation of a semiconductor memory element using an organic semiconductor, in which a performance deterioration material for deteriorating a performance of the organic semiconductor is dispersed, within a lifetime, ~~comprising, in order to activate a performance deterioration material dispersed in the organic semiconductor as the~~ starting device[[,]] being at least one of:

a UV irradiation device for irradiating the performance deterioration material in the organic semiconductor with UV to activate the performance deterioration material; and

an electron beam irradiation device for irradiating the performance deterioration material in the organic semiconductor with electron beam to activate the performance deterioration material.

Claim 25 (New): The semiconductor memory element according to claim 3, wherein the predetermined means is a mechanical punch means.

Claim 26 (New): The semiconductor memory element according to claim 3, wherein the predetermined means is a heating means.

Claim 27 (New): The semiconductor memory element according to claim 3, wherein the predetermined means is a pressurizing means.

Claim 28 (New): The semiconductor memory element according to claim 3, wherein the predetermined means is a light irradiation means.

Claim 29 (New): The semiconductor memory element according to claim 9, wherein the performance deterioration material is encapsulated.

Claim 30 (New): The semiconductor memory element according to claim 10, wherein the performance deterioration material is encapsulated.

Claim 31 (New): The semiconductor memory element according to claim 9, wherein the predetermined means is a pressurizing means.

Claim 32 (New): The semiconductor memory element according to claim 9, wherein the predetermined means is a heating means.

Claim 33 (New): The semiconductor memory element according to claim 10,  
wherein  
the deterioration in the semiconductor circuit portion of the organic semiconductor is  
started by stripping off the seal member.

Claim 34 (New): The semiconductor memory element according to claim 2, wherein  
the semiconductor portion is a semiconductor portion in a range corresponding to a  
predetermined circuit portion of the semiconductor circuit portion.

Claim 35 (New): The semiconductor memory element according to claim 3, wherein  
the semiconductor portion is a semiconductor portion in a range corresponding to a  
predetermined circuit portion of the semiconductor circuit portion.

Claim 36 (New): The semiconductor memory element according to claim 8, wherein  
the semiconductor portion is a semiconductor portion in a range corresponding to a  
predetermined circuit portion of the semiconductor circuit portion.

Claim 37 (New): The semiconductor memory element according to claim 9, wherein  
the semiconductor portion is a semiconductor portion in a range corresponding to a  
predetermined circuit portion of the semiconductor circuit portion.

Claim 38 (New): The semiconductor memory element according to claim 10,  
wherein  
the semiconductor portion is a semiconductor portion in a range corresponding to a  
predetermined circuit portion of the semiconductor circuit portion.

Claim 39 (New): The semiconductor memory element according to claim 34,  
wherein  
the predetermined circuit portion is a data area.

Claim 40 (New): The semiconductor memory element according to claim 35,  
wherein  
the predetermined circuit portion is a data area.

Claim 41 (New): The semiconductor memory element according to claim 36,  
wherein  
the predetermined circuit portion is a data area.

Claim 42 (New): The semiconductor memory element according to claim 37,  
wherein  
the predetermined circuit portion is a data area.

Claim 43 (New): The semiconductor memory element according to claim 38,  
wherein  
the predetermined circuit portion is a data area.

Claim 44 (New): The semiconductor memory element according to claim 34,  
wherein  
the predetermined circuit portion is a management information area.

Claim 45 (New): The semiconductor memory element according to claim 35,  
wherein  
the predetermined circuit portion is a management information area.

Claim 46 (New): The semiconductor memory element according to claim 36,  
wherein  
the predetermined circuit portion is a management information area.

Claim 47 (New): The semiconductor memory element according to claim 37,  
wherein



the predetermined circuit portion is a management information area.

Claim 48 (New):      The semiconductor memory element according to claim 38,  
wherein  
the predetermined circuit portion is a management information area.

Claim 49 (New):      The semiconductor memory element according to claim 34,  
wherein  
the predetermined circuit portion is an electric power shutdown switch.

Claim 50 (New):      The semiconductor memory element according to claim 35,  
wherein  
the predetermined circuit portion is an electric power shutdown switch.

Claim 51 (New):      The semiconductor memory element according to claim 36,  
wherein  
the predetermined circuit portion is an electric power shutdown switch.

Claim 52 (New):      The semiconductor memory element according to claim 37,  
wherein  
the predetermined circuit portion is an electric power shutdown switch.

Claim 53 (New):      The semiconductor memory element according to claim 38,  
wherein  
the predetermined circuit portion is an electric power shutdown switch.

Claim 54 (New):      The semiconductor memory element according to claim 34,  
wherein  
the predetermined circuit portion is an encryption key record area.

Claim 55 (New): The semiconductor memory element according to claim 35,  
wherein

the predetermined circuit portion is an encryption key record area.

Claim 56 (New): The semiconductor memory element according to claim 36,  
wherein

the predetermined circuit portion is an encryption key record area.

Claim 57 (New): The semiconductor memory element according to claim 37,  
wherein

the predetermined circuit portion is an encryption key record area.

Claim 58 (New): The semiconductor memory element according to claim 38,  
wherein

the predetermined circuit portion is an encryption key record area.

Claim 59 (New): A record medium comprising a semiconductor memory element,  
wherein

the semiconductor memory element comprises a substrate; a semiconductor circuit portion made of an organic semiconductor disposed on the substrate; and a protection circuit disposed adjacent to the semiconductor circuit portion, the protection portion being made of a material in which a crack extending to the semiconductor circuit portion is formed after a predetermined means performs.

Claim 60 (New): A record medium comprising a semiconductor memory element,  
wherein

the semiconductor memory element comprises a substrate; a semiconductor circuit portion comprising an organic semiconductor disposed on the substrate; a protection portion disposed adjacent to the semiconductor circuit portion and including a window portion; and a strippable seal member for sealing the window portion of the protection portion.

Claim 61 (New): A record medium comprising a semiconductor memory element, wherein

the semiconductor memory element comprises a substrate; a semiconductor circuit portion made of an organic semiconductor disposed on the substrate; a protection portion disposed adjacent to the semiconductor circuit portion; and a performance deterioration portion including a performance deterioration material for deteriorating a performance of the organic semiconductor and disposed adjacent to the protection portion, the protection portion being made of a material in which a crack extending to the semiconductor circuit portion is formed after a predetermined means performs.

Claim 62 (New): A record medium comprising a semiconductor memory element, wherein

the semiconductor memory element comprising a substrate; a semiconductor circuit portion disposed on the substrate and made of an organic semiconductor including a performance deterioration material for deteriorating a performance of the organic semiconductor after the performance deterioration is activated; and a protection portion disposed adjacent to the semiconductor circuit portion, the performance deterioration material being activated by a predetermined means.

Claim 63 (New): A record medium comprising a semiconductor memory element, wherein

the semiconductor memory element comprises a substrate; a semiconductor circuit portion disposed on the substrate and made of an organic semiconductor including a performance deterioration material for deteriorating a performance of the organic semiconductor after the performance deterioration is activated; and a film disposed adjacent to the semiconductor circuit portion, capable of obtaining light transmissive property due to an irradiation of light having a predetermined wavelength thereon, the performance deterioration material being activated by a predetermined means.

Claim 64 (New):      A record medium comprising a semiconductor memory element, wherein

the semiconductor memory element comprises a substrate; a semiconductor circuit portion disposed on the substrate and made of an organic semiconductor including a performance deterioration material for deteriorating a performance of the organic semiconductor after the performance deterioration is activated; a protection portion disposed adjacent to the semiconductor circuit portion and having a window portion; and a strippable seal member for sealing the window portion of the protection portion.

Claim 65 (New):      A memory device comprising:  
memory elements for storing data, the memory elements comprising circuit portions including an organic semiconductor material; and

means for causing deterioration over time of the organic semiconductor material to thereby determine a time period during which data stored in the memory elements can be reproduced,

wherein the deteriorating-causing means is arranged so that the deterioration caused thereby can begin at a specified time after fabrication of the memory device.

Claim 66 (New):      The memory device according to claim 65, wherein the memory elements are organized into two or more storage areas and the deterioration-causing means is provided separately for each storage area, whereby data stored in memory cells in different storage areas can be reproduced for different time periods.

Claim 67 (New):      The memory device according to claim 65, wherein the memory device is embodied as a memory card.